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Optimization of materials for Metal-Insulator-Metal resistance devices -Memresistor

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Optimization of thin films (5-30 nm thick) with specific and interesting characteristics for the charge transfer process in metal-insulator-metal nanostructures to obtain controlled switching characteristics for integration into nanostructures of artificial neural networks based on memristors and understanding the electrical transport mechanisms in the insulating material. As electrical conductance depends on the amount of electrical charges that have passed through them, this feature makes the device an ideal tool for mimicking a biological synapse.

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